SENSITRON

SEMICONDUCTOR

MURC620

Technical Data Data Sheet 4857, Rev.-

MURC620 Ultrafast Silicon Die

Applications:

• Switching Power Supply • General Purpose • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Glass-Passivated
- Epitaxial Construction.
- Low Reverse Leakage Current
- High Surge Current Capability
- Low Forward Voltage Drop
- Fast Reverse-Recovery Behavior

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	200	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =100°C, rectangular wave form	6.0	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	60	A
Max. Junction Capacitance	CJ	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz, V _{SIG} = 50mV (p-p)	75	pF
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

Electrical Characteristics:

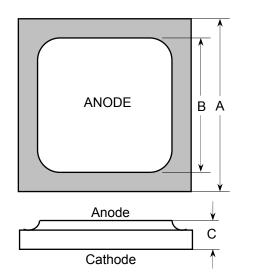
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	V_{F1}	@ 6.0A, Pulse, T _J = 25 °C	1.2	V
	V _{F2}	@ 6.0A, Pulse, T _J = 100 °C	1.0	V
Max. Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	6	μA
	I _{R2}	@V _R = 0.8V _R T _J = 100 °C	60	μA
Max Reverse Recovery Time	t _{rr}	I _F =0.5A, I _R =1.0A, I _{REC} =0.25A	25	nS
Max Reverse Recovery Time	t _{rr}	l _F =6A, di/dt=200A/µs	35	nS

* Pulse Width < 300µs, Duty Cycle <2%

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Dimensions in inches (mm)



Top side metalization: AI - 25 kÅ minimum or Ti/Ni/Ag - 30 kÅ minimum

Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum. Bottom side is cathode, top side is anode.

Die type	Area (mil ²)	Dimension A ⁽¹⁾	Dimension B ⁽¹⁾	Dimension C ⁽²⁾
		Inch (millimeter)	Inch (millimeter)	Inch (millimeter)
Si p-n die	85 x 85	0.085 (2.159)	0.069 (1.753)	0.009 (0.229)

⁽¹⁾ Tolerance is ± 0.003" (0.076 mm) ⁽²⁾ Tolerance is ± 0.001" (0.025 mm)

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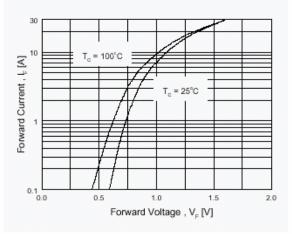
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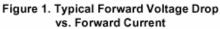
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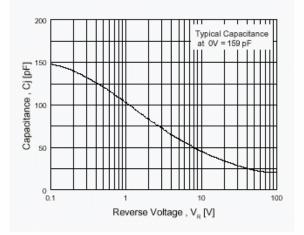


Figure 3. Typical Junction Capacitance

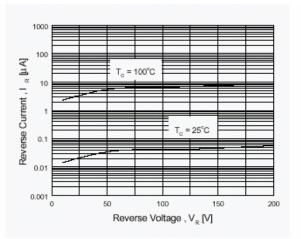
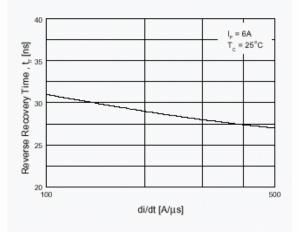
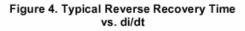


Figure 2. Typical Reverse Current vs. Reverse Voltage





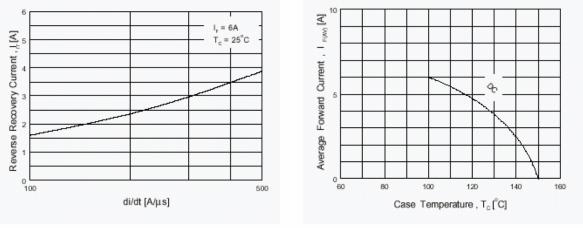


Figure 5. Typical Reverse Recovery Current vs. di/dt

Figure 6. Forward Current Derating Curve